



IRFP360LCPBF Information



For Reference Only

Part Number IRFP360LCPBF **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 400V 23A TO-247AC

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFP360LCPBF Specifications

Manufacturer Part Number IRFP360LCPBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 400V Current - Continuous Drain (Id) @ 25°C 23A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 280W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 400V Current - Continuous Drain (Id) @ 25°C 23A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 280W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Manufacturer Part Number	IRFP360LCPBF
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)400VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)280W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)400VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)280W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 400V 23A (Tc) 23A (Tc) 10V 4V @ 250μA 110nC @ 10V 3400pF @ 25V ±30V FET Geature - Power Dissipation (Max) 280W (Tc) 280W (Tc) Through Hole To-247-3 Package / Case	Series	-
Drain to Source Voltage (Vdss)400VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)280W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 280W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 14A, 10V Operating Temperature Supplier Device Package TO-247-3 Package / Case TO-247-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 280W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Drain to Source Voltage (Vdss)	400V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 250μA 110nC @ 10V 3400pF @ 25V ±30V E30V E30V E30V E30V To-247-3 Through Hole TO-247-3	Current - Continuous Drain (Id) @ 25°C	23A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Jenus Single Company Through Hole Supplier Device Package TO-247-3 Package / Case 110nC @ 10V 3400pF @ 25V 280W To 280W To 280W To 280W To 280W To 270 Through Hole Through Hole	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)280W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	110nC @ 10V
FET Feature - Power Dissipation (Max) 280W (Tc) Rds On (Max) @ Id, Vgs 200 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	3400pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 14A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs200 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Power Dissipation (Max)	280W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	200 mOhm @ 14A, 10V
Supplier Device Package TO-247-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247-3
Report errors?	Package / Case	TO-247-3
		Report errors?

IRFP360LCPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFP360LCPBF Payment Methods



















IRFP360LCPBF Shipping Methods













If you have any question about IRFP360LCPBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com